

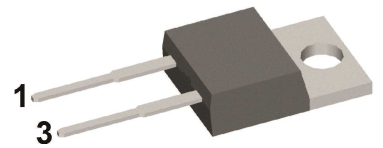
FRED

V_{RRM}	=	1000 V
I_{FAV}	=	12 A
t_{rr}	=	45 ns

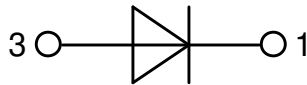
Fast Recovery Epitaxial Diode Single Diode

Part number

DSEI12-10A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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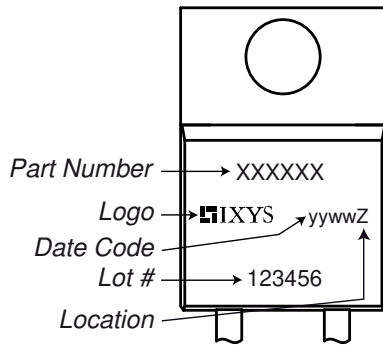


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1000	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1000	V	
I_R	reverse current, drain current	$V_R = 1000\text{ V}$	$T_{VJ} = 25^{\circ}C$		250	μA	
		$V_R = 800\text{ V}$	$T_{VJ} = 125^{\circ}C$		4	mA	
V_F	forward voltage drop	$I_F = 12\text{ A}$	$T_{VJ} = 25^{\circ}C$		2.68	V	
		$I_F = 24\text{ A}$			3.02	V	
		$I_F = 12\text{ A}$	$T_{VJ} = 150^{\circ}C$		2.12	V	
		$I_F = 24\text{ A}$			2.57	V	
I_{FAV}	average forward current	$T_C = 100^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		12	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.72	V	
r_F	slope resistance				34	m Ω	
R_{thJC}	thermal resistance junction to case				1.6	K/W	
R_{thCH}	thermal resistance case to heatsink			0.50		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		78	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}C$		75	A	
C_J	junction capacitance	$V_R = 500\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		8	pF	
I_{RM}	max. reverse recovery current	} $I_F = 12\text{ A}; V_R = 540\text{ V}$ $-di_F/dt = 100\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}C$		4	A	
			$T_{VJ} = 100^{\circ}C$		7	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		90	ns	
			$T_{VJ} = 100^{\circ}C$		150	ns	



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI12-10A	DSEI12-10A	Tube	50	434434

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$

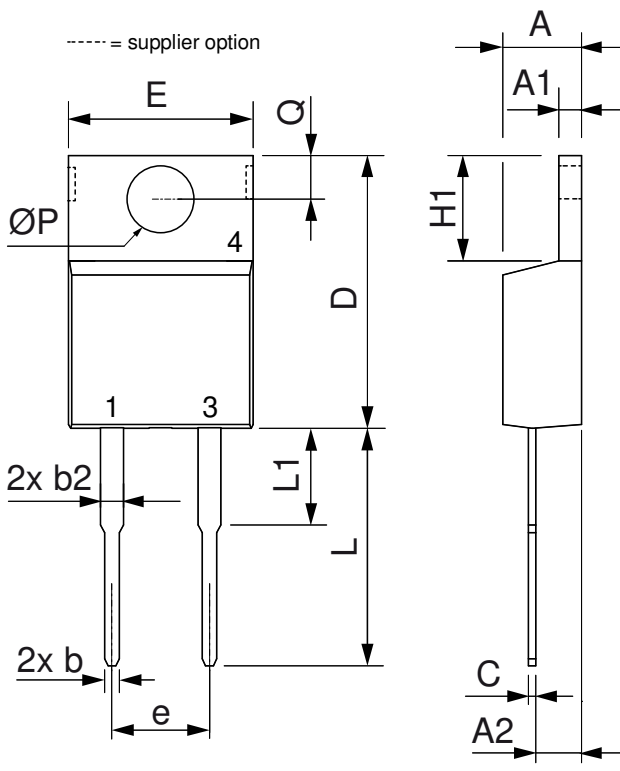


Fast Diode

$V_{0\ max}$	threshold voltage	1.72	V
$R_{0\ max}$	slope resistance *	31	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





Fast Diode

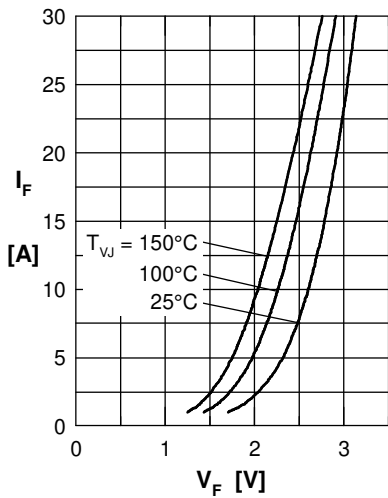


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

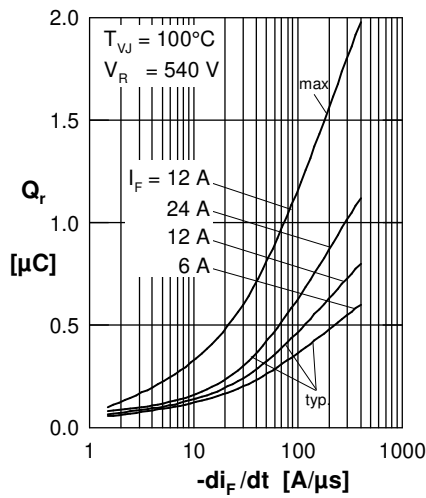


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

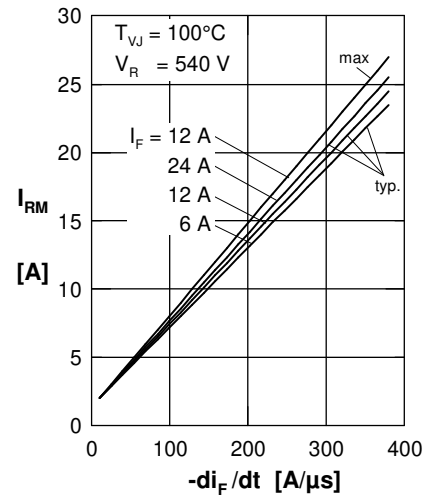


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

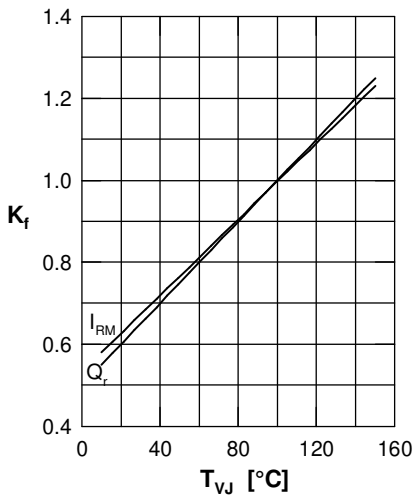


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

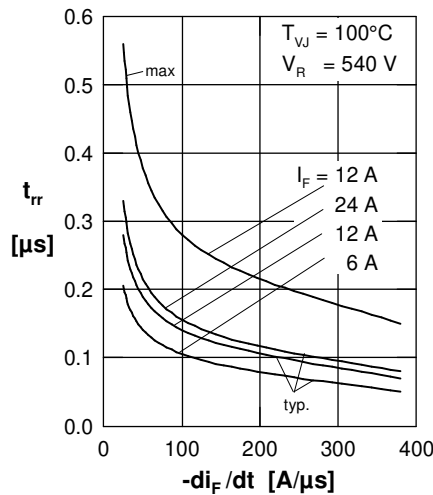


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

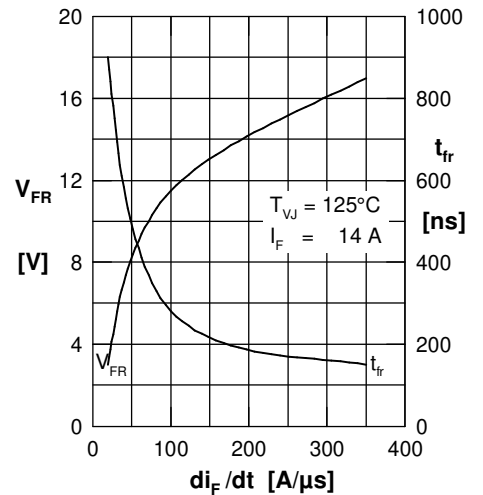


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

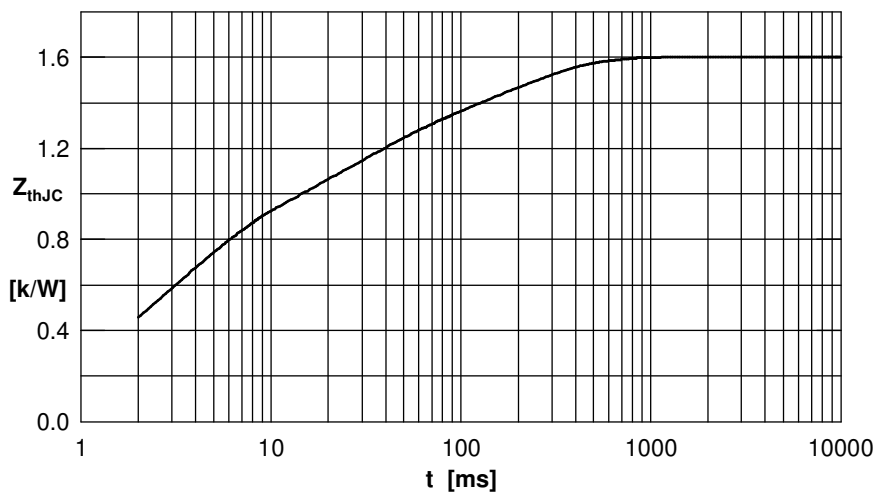


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.400	0.180
4	0.400	0.024
5	0.680	0.003

单击下面可查看定价，库存，交付和生命周期等信息

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